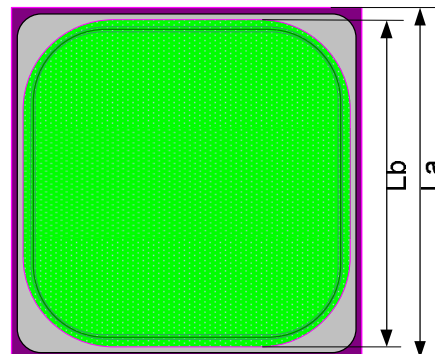


## 2SF292200CYY

### 2SF292200CYY ULTRAFAST RECOVERY DIODE CHIPS

#### DESCRIPTION

- Ø 2SF292200CYY is a ultrafast recovery diode chips fabricated in silicon epitaxial planar technology;
- Ø Ultrafast recovery times;
- Ø High current capability;
- Ø High surge current capability;
- Ø Low forward voltage drop;
- Ø Low reverse current leakage;
- Ø Top metal is Ag, Back metal is Ag;
- Ø Chip Size: 2920 $\mu$ m X 2920 $\mu$ m;
- Ø Chip Thickness: 280 $\pm$ 20 $\mu$ m;



Chip Topography and Dimensions

La: Chip Size:2920  $\mu$ m;

Lb: Pad Size: 2840  $\mu$ m;

#### ORDERING SPECIFICATIONS

| Product Name | Specification                        |
|--------------|--------------------------------------|
| 2SF292200CYY | For Au and AlSi wire bonding package |

#### ABSOLUTE MAXIMUM RATINGS

| Parameters                                 | Symbol | Ratings | Unit |
|--------------------------------------------|--------|---------|------|
| Maximum Repetitive Peak Reverse Voltage    | VRRM   | 200     | V    |
| Average Forward Rectified Current@Tc=150°C | IFAV   | 15      | A    |
| Peak Forward Surge Current@8.3ms           | IFSM   | 200     | A    |
| Maximum Operation Junction Temperature     | TJ     | 175     | °C   |
| Storage Temperature Range                  | TSTG   | -55~175 | °C   |

#### ELECTRICAL CHARACTERISTICS (Tamb = 25 °C)

| Parameters            | Symbol | Test Conditions           | Min. | Max. | Unit    |
|-----------------------|--------|---------------------------|------|------|---------|
| Reverse Voltage       | VBR    | IR=50 $\mu$ A             | 200  | --   | V       |
| Forward Voltage       | VF     | IF=15A                    | --   | 1.05 | V       |
| Reverse Current       | IR     | VR=200V                   | --   | 10   | $\mu$ A |
| Reverse recovery time | Trr    | IF=1A, di/dt=50A/ $\mu$ s | --   | 35   | ns      |